Preferred Device

General Purpose Transistors

PNP Silicon



ON Semiconductor™

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MAXIMUM RATINGS Rating Symbol Value Unit Collector-Emitter Voltage 40 Vdc VCEO Collector-Base Voltage 40 Vdc VCBO Vdc Emitter-Base Voltage 5.0 VEBO Collector Current - Continuous 200 mAdc IC Total Device Dissipation P_D @ T_A = 25°C 625 mW Derate above 25°C 5.0 mW/°C **Total Power Dissipation** P_D 250 mW @ $T_A = 60^{\circ}C$ **Total Device Dissipation** PD @ $T_{C} = 25^{\circ}C$ 1.5 Watts Derate above 25°C 12 mW/°C Operating and Storage Junction -55 to °C TJ, Tstg

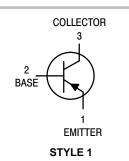
THERMAL CHARACTERISTICS (Note 1.)

Temperature Range

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R _θ JC	83.3	°C/W

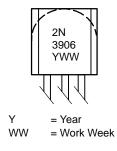
+150

1. Indicates Data in addition to JEDEC Requirements.





MARKING DIAGRAMS



ORDERING INFORMATION

Device	Package	Shipping
2N3906	TO-92	5000 Units/Box
2N3906RLRA	TO-92	2000/Tape & Reel
2N3906RLRE	TO-92	2000/Tape & Reel
2N3906RLRM	TO-92	2000/Ammo Pack
2N3906RLRP	TO-92	2000/Ammo Pack
2N3906RL1	TO-92	2000/Tape & Reel
2N3906ZL1	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 2.) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _(BR) CEO	40	-	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \ \mu Adc$, $I_E = 0$)	V(BR)CBO	40	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \ \mu Adc$, $I_C = 0$)	V(BR)EBO	5.0	-	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	IBL	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		-	50	nAdc

ON CHARACTERISTICS (Note 2.)

$ \begin{array}{l} \mbox{DC Current Gain} \\ (I_C = 0.1 \mbox{ mAdc}, V_{CE} = 1.0 \mbox{ Vdc}) \\ (I_C = 1.0 \mbox{ mAdc}, V_{CE} = 1.0 \mbox{ Vdc}) \\ (I_C = 10 \mbox{ mAdc}, V_{CE} = 1.0 \mbox{ Vdc}) \\ (I_C = 50 \mbox{ mAdc}, V_{CE} = 1.0 \mbox{ Vdc}) \\ (I_C = 100 \mbox{ mAdc}, V_{CE} = 1.0 \mbox{ Vdc}) \\ \end{array} $	hfe	60 80 100 60 30	_ 300 _	-
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$	V _{CE(sat)}	- -	0.25 0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc

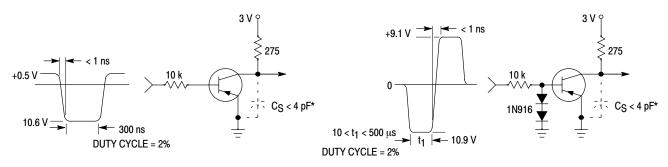
SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product	fT			MHz
(I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)		250	-	
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C _{obo}	-	4.5	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0, f = 1.0 \text{ MHz}$)	C _{ibo}	-	10	pF
Input Impedance (I _C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio	h _{re}			X 10 ⁻⁴
(I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		0.1	10	
Small–Signal Current Gain	h _{fe}			-
(I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		100	400	
Output Admittance (I _C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h _{oe}	3.0	60	μmhos
Noise Figure	NF			dB
$(I_{C} = 100 \ \mu \text{Adc}, \ V_{CE} = 5.0 \ \text{Vdc}, \ R_{S} = 1.0 \ \text{k}\Omega, \ f = 1.0 \ \text{kHz})$		-	4.0	

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,	td	-	35	ns
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	tr	-	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _s	_	225	ns
Fall Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _f	_	75	ns

2. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2%.

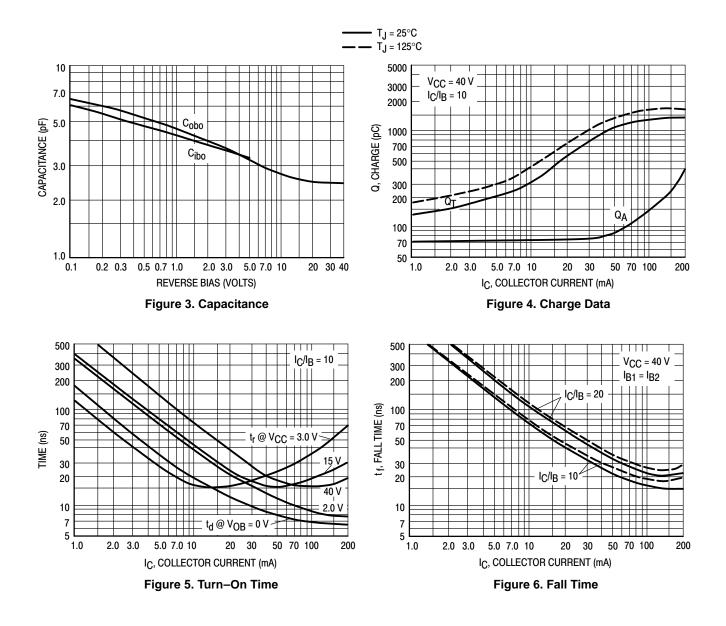


* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

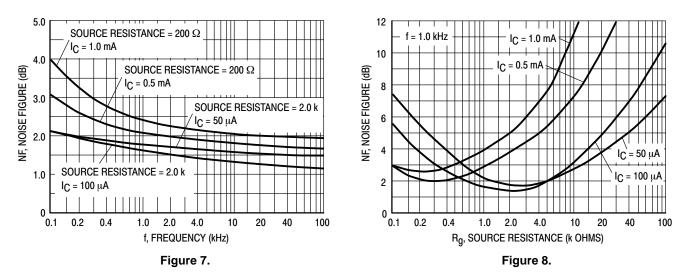
Figure 2. Storage and Fall Time Equivalent Test Circuit

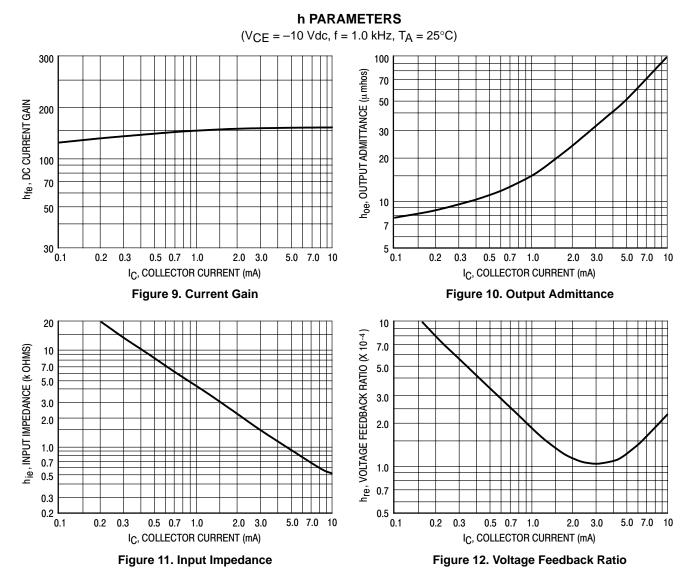
TYPICAL TRANSIENT CHARACTERISTICS



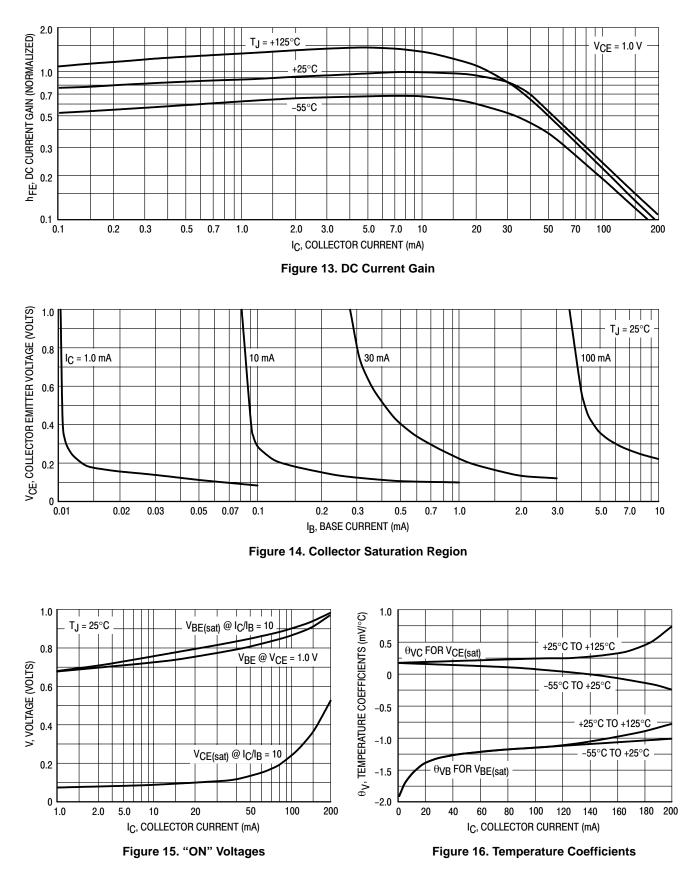
TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

(V_{CE} = -5.0 Vdc, T_A = 25° C, Bandwidth = 1.0 Hz)



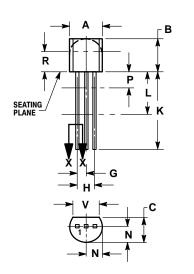






PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL**





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUL OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Η	0.095	0.105	2.42	2.66
L	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE

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<u>Notes</u>

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